

STRUCTURE AND METHOD FOR FABRICATING GaN DEVICES  
UTILIZING THE FORMATION OF A COMPLIANT SUBSTRATE

ABSTRACT

High quality epitaxial layers of GaN can be grown overlying large silicon wafers (200) by forming an amorphous layer (210) on the substrate. The amorphous layer dissipates strain and permits the growth of a high quality GaN layer (208). Any lattice mismatch between the GaN layer and the underlying substrate is taken care of by the amorphous layer.

FIG. 10: 509200